DISCRETE SEMICONDUCTORS

DATA SHEET

BTA216 series D, E and F Three quadrant triacs guaranteed commutation

Product specification

September 2018



WeEn Semiconductors Product specification

Three quadrant triacs guaranteed commutation

BTA216 series D, E and F

GENERAL DESCRIPTION

Passivated guaranteed commutation triacs in a plastic envelope intended for use in motor control circuits or with other highly inductive loads. These devices balance the requirements of commutation performance and gate sensitivity. The "sensitive gate" E series and "logic level" D series are intended for interfacing with low power drivers, including micro controllers.

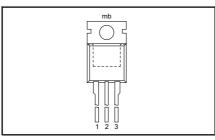
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
	BTA216- BTA216- BTA216-	600D 600E 600F	
V_{DRM}	Repetitive peak off-state	600	V
I _{T(RMS)} I _{TSM}	voltages RMS on-state current Non-repetitive peak on-state	16 140	A A

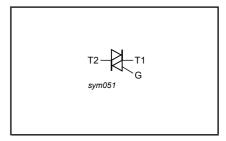
PINNING - TO220AB

PIN	DESCRIPTION
1	main terminal 1
2	main terminal 2
3	gate
tab	main terminal 2

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DRM}	Repetitive peak off-state voltages		-	600¹	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 99 °C	-	16	Α
I _{TSM}	Non-repetitive peak on-state current	full sine wave; T _j = 25 °C prior to surge			
12.	12.	t = 20 ms t = 16.7 ms	-	140 150	A A A ² s
l²t dl _⊤ /dt	l ² t for fusing Repetitive rate of rise of on-state current after	$egin{aligned} t = 10 \text{ ms} \\ I_{TM} = 20 \text{ A}; I_{G} = 0.2 \text{ A}; \\ dI_{G}/dt = 0.2 \text{ A}/\mu\text{s} \end{aligned}$	-	98 100	A²s A/μs
I _{GM} P _{GM}	triggering Peak gate current Peak gate power		-	2 5	A W
$P_{G(AV)}^GMN$	Average gate power	over any 20 ms period	-	0.5	W
${\mathsf T}_{stg} \atop {\mathsf T}_{\mathsf j}$	Storage temperature Operating junction temperature		-40 -	150 125	Ç

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¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 $A/\mu s$.

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THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th j-mb}$ $R_{th j-a}$	Thermal resistance junction to mounting base Thermal resistance junction to ambient	full cycle half cycle in free air	- - -	- - 60	1.2 1.7 -	K/W K/W K/W

STATIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.		MAX.		UNIT
		BTA216-		D	Е	F	
I _{GT}	Gate trigger current ²	$V_{D} = 12 \text{ V}; I_{T} = 0.1 \text{ A}$		_			
		T2+ G+ T2+ G-	-	5 5 5	10 10	25 25	mA mA
		T2- G-	-	5	10	25	mA
I _L	Latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	_	15	25	30	mA
		T2+ G-	-	25	30	40	mA
		T2- G-	-	25	30	40	mA
I _H	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	15	25	30	mA
					D, E, F		
V _T	On-state voltage	$I_{T} = 20 \text{ A}$	-		1.5		V
V_{GT}	Gate trigger voltage	$\dot{V}_D = 12 \text{ V}; I_T = 0.1 \text{ A} V_D = 400 \text{ V}; I_T = 0.1 \text{ A};$	- 0.25		1.5		V
		$T_i = 125 ^{\circ}\text{C}$	0.23		_		
I_D	Off-state leakage current	$V_D = V_{DRM(max)}$; $T_j = 125 ^{\circ}C$	-		0.5		mA

DYNAMIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS		MIN.	MAX.	UNIT	
		BTA216-	D	E	F		
dV _D /dt	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(max)};$ $T_j = 110 ^{\circ}C;$ exponential waveform; gate open circuit	30	60	70	-	V/μs
dl _{com} /dt	Critical rate of change of commutating current	$V_{DM} = 400 \text{ V}; T_j = 125 \text{ °C};$ $I_{T(RMS)} = 16 \text{ A};$ $dV_{com}/dt = 10 \text{V}/\mu\text{s}; \text{ gate}$	2.5	6.2	18	-	A/ms
dl _{com} /dt	Critical rate of change of commutating current	open circuit $V_{DM} = 400 \text{ V}; T_j = 125 ^{\circ}\text{C};$ $I_{T(RMS)} = 16 \text{ A};$ $dV_{com}/dt = 0.1 \text{V}/\mu\text{s};$ gate open circuit	12	20	50	-	A/ms

² Device does not trigger in the T2-, G+ quadrant.

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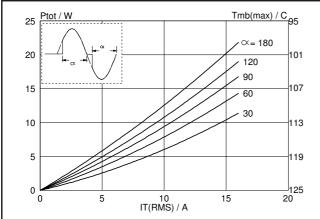


Fig.1. Maximum on-state dissipation, P_{tot} , versus rms on-state current, $I_{T(RMS)}$, where α = conduction angle.

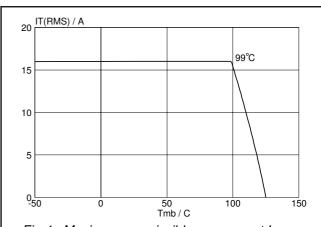


Fig.4. Maximum permissible rms current $I_{T(RMS)}$, versus mounting base temperature T_{mb} .

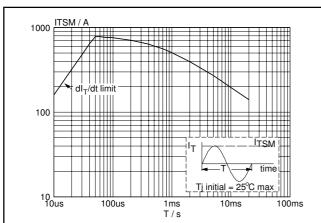


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \le 20$ ms.

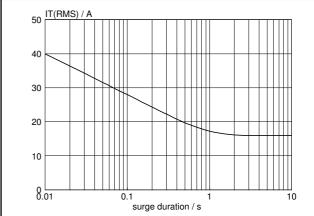


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, f = 50 Hz; $T_{mb} \le 99$ °C.

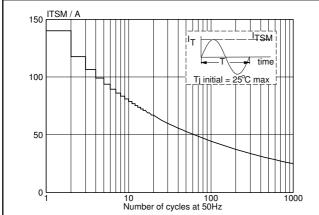


Fig.3. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, f = 50 Hz.

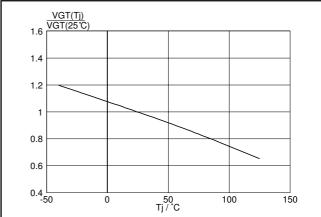
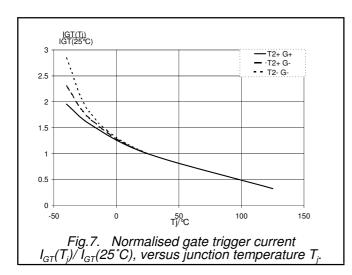


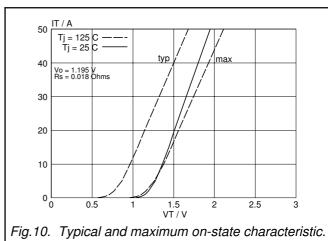
Fig.6. Normalised gate trigger voltage $V_{GT}(T_j)/V_{GT}(25^{\circ}C)$, versus junction temperature T_{j} .

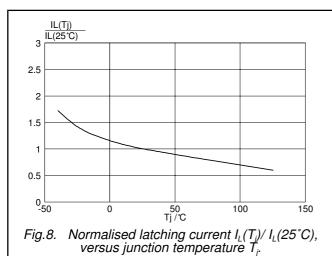
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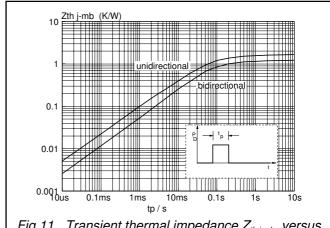
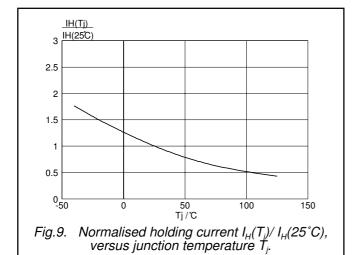


Fig.11. Transient thermal impedance $Z_{th j-mb}$, versus pulse width t_o.



dlcom/dt (A/ms) 100 F TYPE E TYPE D TYPE 20 140 Tj/°C

Fig.12. Minimum, critical rate of change of commutating current dI_{com}/dt versus junction temperature, $dV_{com}/dt = 10V/\mu s$.

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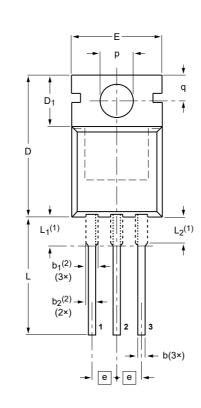
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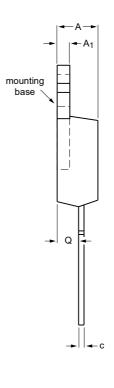
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MECHANICAL DATA

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78





0 5 10 mm

DIMENSIONS (mm are the original dimensions)

UNIT	Α	A ₁	b	b ₁ ⁽²⁾	b ₂ ⁽²⁾	С	D	D ₁	E	е	L	L ₁ ⁽¹⁾	L ₂ ⁽¹⁾ max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

- Lead shoulder designs may vary.
 Dimension includes excess dambar.

OUTLINE		REFERENCES				ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13

Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина,

дом 2, корпус 4, литера А.